

Features

- Trench Power LV MOSFET Technology
- High Density Cell Desihn for Low $R_{DS(on)}$
- Moisture Sensitivity Level 1
- Halogen Free. "Green" Device (Note 1)
- Epoxy Meets UL 94 V-0 Flammability Rating
- Lead Free Finish/RoHS Compliant ("P" Suffix Designates RoHS Compliant. See Ordering Information)

Maximum Ratings

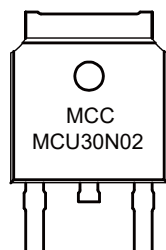
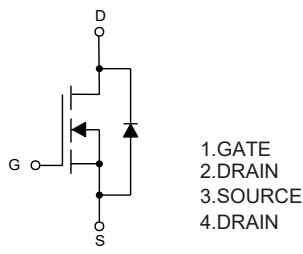
- Operating Junction Temperature Range : -55°C to +175°C
- Storage Temperature Range: -55°C to +175°C
- Thermal Resistance: 50°C/W Junction to Ambient^(Note 2)
- Thermal Resistance: 5°C/W Junction to Case

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DS}	20	V
Gate-Source Voltlage	V_{GS}	±10	V
Continuous Drain Current	I_D	$T_C=25^\circ C$	30
		$T_C=100^\circ C$	21
Pulsed Drain Current ^(Note3)	I_{DM}	120	A
Total Power Dissipation ^(Note4)	P_D	30	W
Single Pulse Avalanche Energy ^(Note5)	E_{AS}	50	mJ

Note:

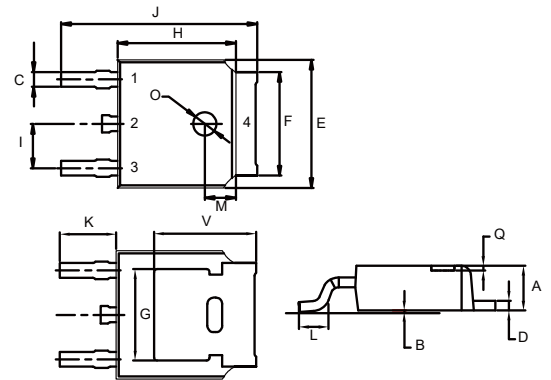
1. Halogen free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
2. The value of RθJA is measured with the device mounted on 1in2 FR-4 board with 2oz. Copper, in a still air environment with $T_A = 25^\circ C$.
3. Repetitive rating; pulse width limited by max. junction temperature.
4. P_D is based on max. junction temperature, using junction-case thermal resistance.
5. $T_J=25^\circ C$, $V_{DD}=15V$, $V_{GS}=5V$, $R_G=25\Omega$, $L=0.5mH$.

Pin Configuration



N-CHANNEL MOSFET

DPAK



DIMENSIONS

DIM	INCHES		MM		NOTE
	MIN	MAX	MIN	MAX	
A	0.087	0.094	2.20	2.40	
B	0.000	0.005	0.00	0.13	
C	0.026	0.034	0.66	0.86	
D	0.018	0.023	0.46	0.58	
E	0.256	0.264	6.50	6.70	
F	0.201	0.215	5.10	5.46	
G	0.190		4.83		TYP.
H	0.236	0.244	6.00	6.20	
I	0.086	0.094	2.18	2.39	
J	0.386	0.409	9.80	10.40	
K	0.114		2.90		TYP.
L	0.055	0.067	1.40	1.70	
M	0.063		1.60		TYP.
O	0.043	0.051	1.10	1.30	
Q	0.000	0.012	0.00	0.30	
V	0.211		5.35		TYP.

ELECTRICAL CHARACTERISTICS (Ta=25°C unless otherwise specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Static Characteristics						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS}=0V, I_D=250\mu A$	20			V
Gate-Source Leakage Current	I_{GSS}	$V_{DS}=0V, V_{GS}=\pm 10V$			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=20V, V_{GS}=0V$			1	μA
Gate-Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	0.45	0.62	1	V
Drain-Source On-Resistance	$R_{DS(on)}$	$V_{GS}=4.5V, I_D=15A$		5.8	7	m Ω
		$V_{GS}=2.5V, I_D=7A$		7.1	9	
		$V_{GS}=1.8V, I_D=3A$		10	14	
Gate Resistance	R_g	$V_{GS}=0V, f=1MHz$		2.1		Ω
Dynamic Characteristics						
Continuous Body Diode Current	I_S				30	A
Diode Forward Voltage	V_{SD}	$V_{GS}=0V, I_S=15A$			1.2	V
Body Diode Reverse Recovery Time	t_{rr}	$I_F=6.5A, di/dt=100A/us$		24		ns
Body Diode Reverse Recovery charge	Q_{rr}			11		nC
Dynamic Characteristics						
Input Capacitance	C_{iss}	$V_{DS}=10V, V_{GS}=0V, f=1MHz$		1361		pF
Output Capacitance	C_{oss}			230		
Reverse Transfer Capacitance	C_{riss}			209		
Total Gate Charge	Q_g	$V_{DS}=10V, V_{GS}=8V, I_D=10A$		15.7		nC
Gate-Source Charge	Q_{gs}			1.5		
Gate-Drain Charge	Q_{gd}			5.3		
Turn-On Delay Time	$t_{d(on)}$	$V_{DD}=10V, V_{GS}=8V, R_G=4.5\Omega, I_D=10A$		5		ns
Turn-On Rise Time	t_r			11		
Turn-Off Delay Time	$t_{d(off)}$			46		
Turn-Off Fall Time	t_f			20		

Curve Characteristics

Fig. 1 Typical Output Characteristics

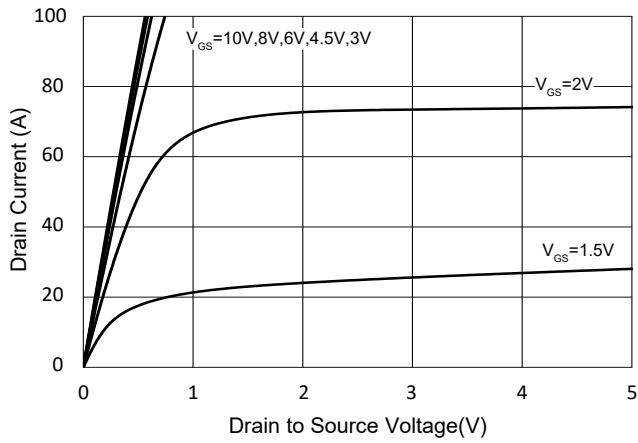


Fig.2 Transfer Characteristic

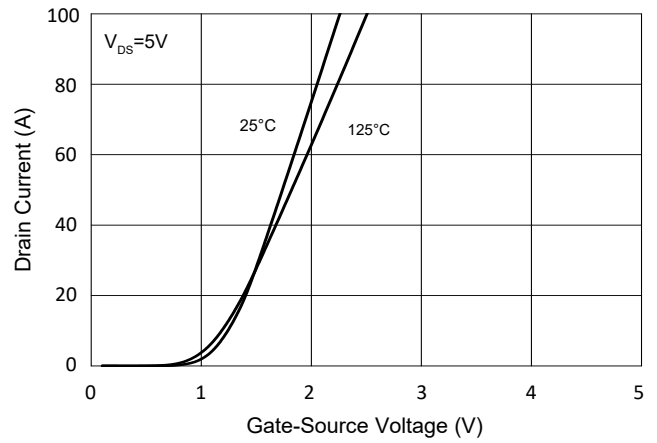


Fig.3 Rds-on-Vgs

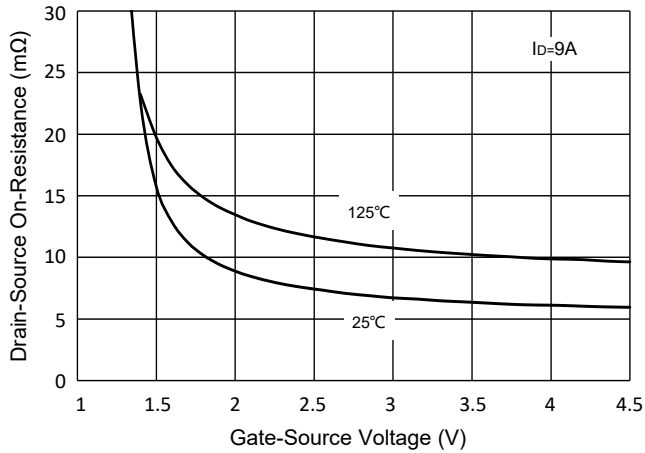


Fig. 4 - $R_{DS(ON)} - I_D$

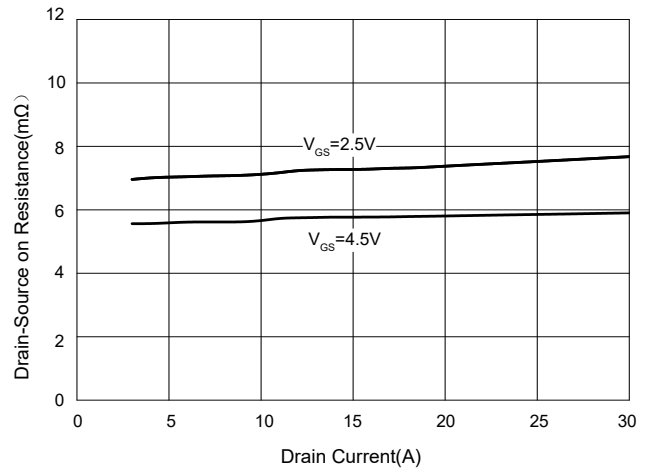


Fig.5 Capacitance Characteristics

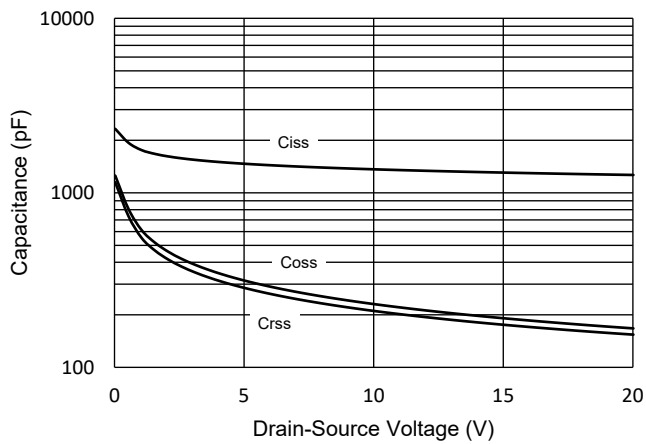
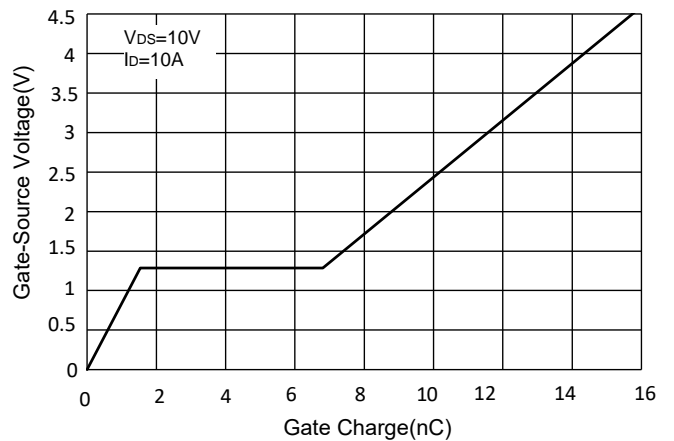


Fig.6 Gate Charge



Curve Characteristics

Fig.7 Normalized Threshold Voltage

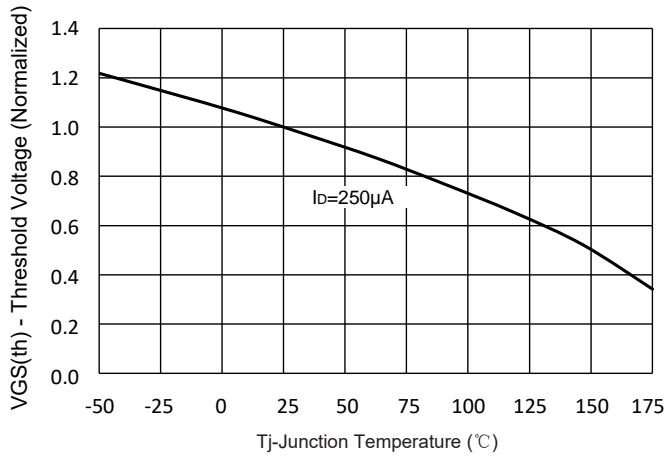


Fig. 8 - Normalized Threshold voltage

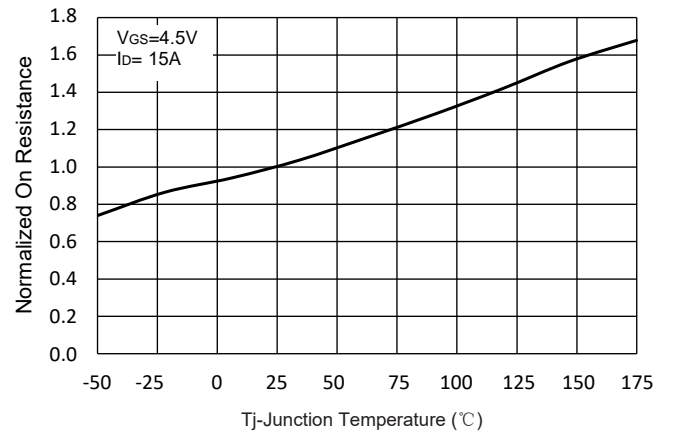


Fig.9 IS-VSD

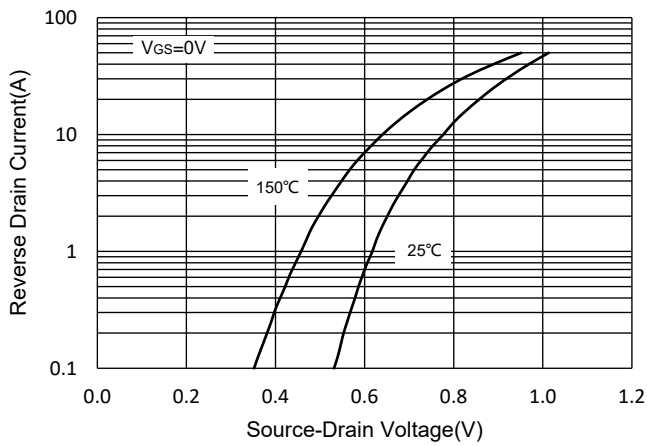


Fig. 10 - Drain Current

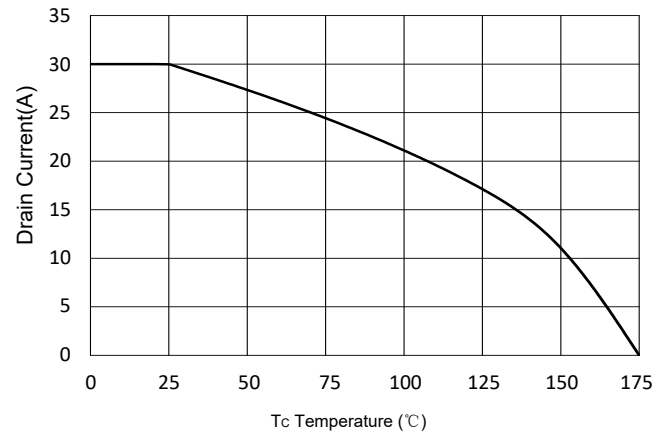
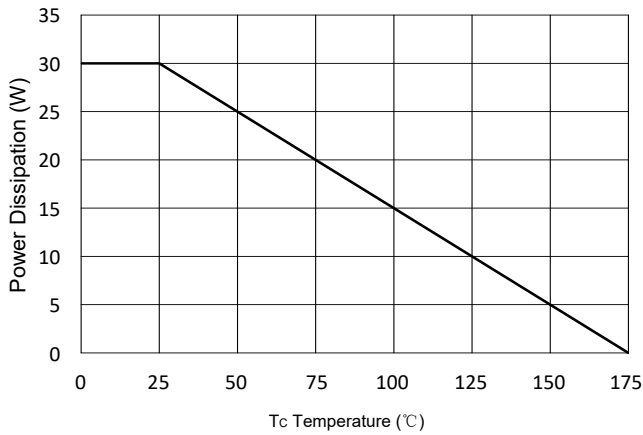


Fig.11 Power Dissipation



Curve Characteristics

Fig. 12 - Safe Operation Area

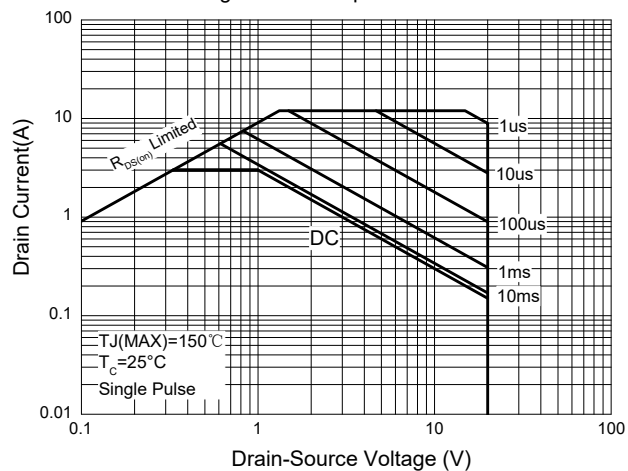
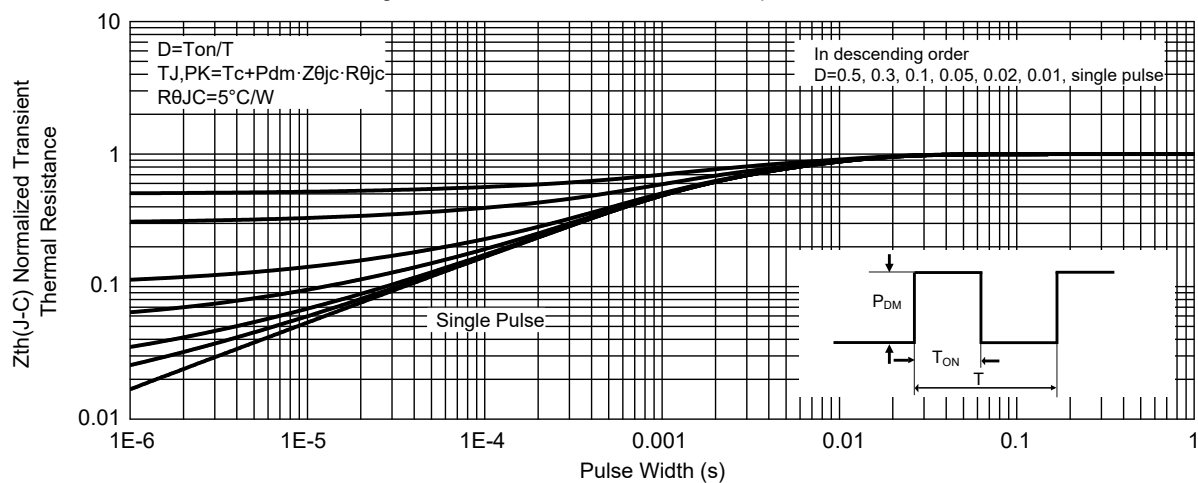


Fig. 13 - Normalized Transient Thermal Impedance



Ordering Information

Device	Packing
Part Number-TP	Tape&Reel: 2.5Kpcs/Reel

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